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In the Drawings:

Please approve the proposed drawing revisions as shown in the attached proposed drawing sheets. Additionally, a further sectional view corresponding to Figure 5 is attached. Should the Examiner require inclusion of such a Figure in view of the following remarks, approval of the same is respectfully requested. Further, a copy of the original informal drawing of Figure 5 of the parent application 09/711,725, now U. S. Patent 6,472,258, is also attached. This informal drawing shows a surface connection by a double line above the region indicated by reference numeral 50. Should the Examiner require inclusion of this feature in Figure 5 of the present application, approval thereof is also respectfully requested.

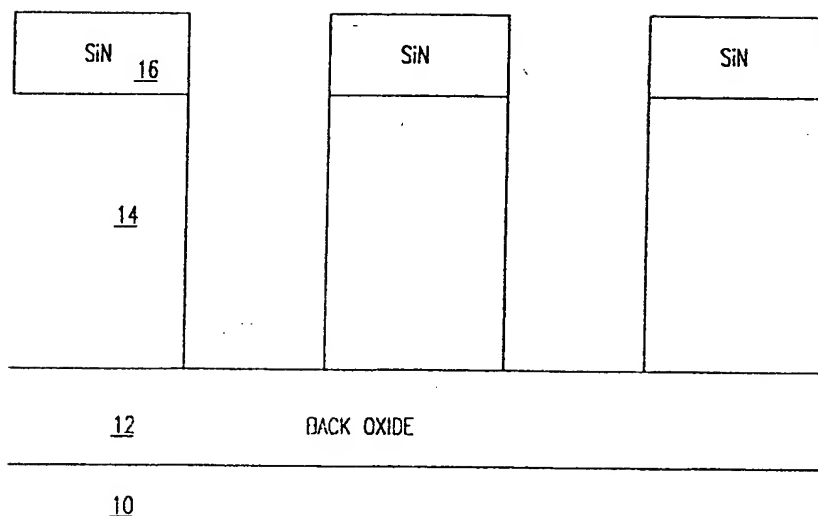


FIG. 1
(SECTION AA')

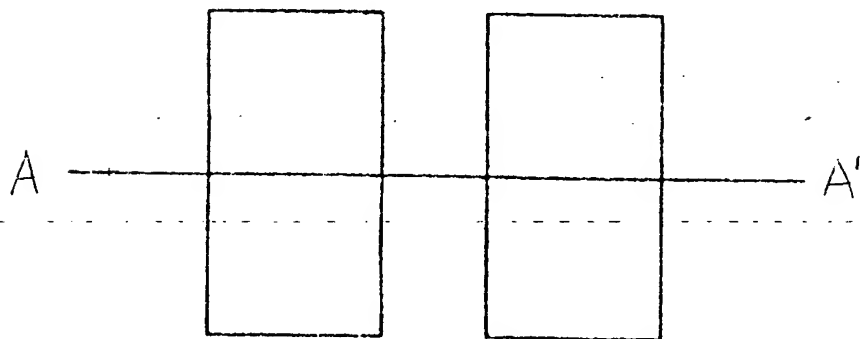


FIG. 1A

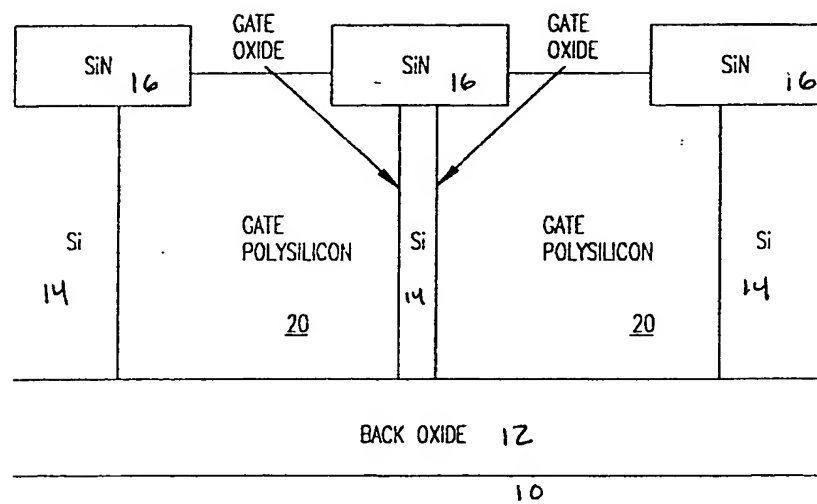


FIG. 2
(SECTION AA')

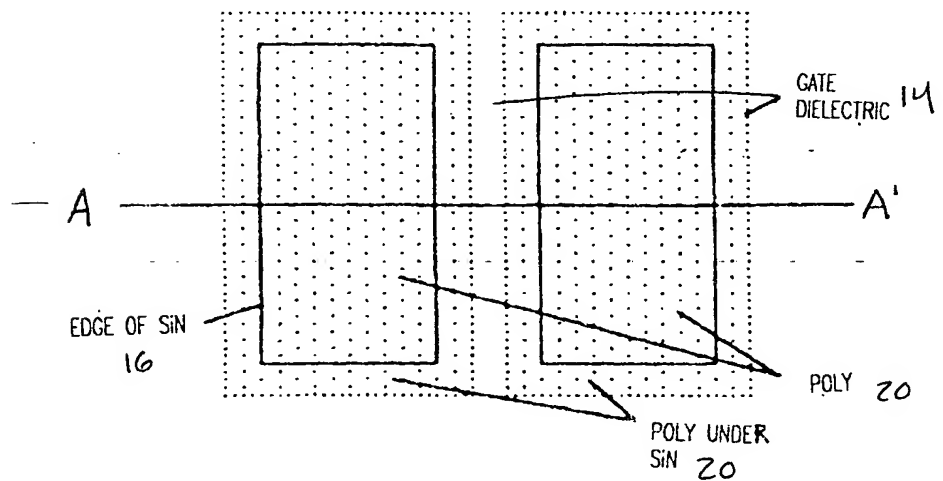


FIG. 2A

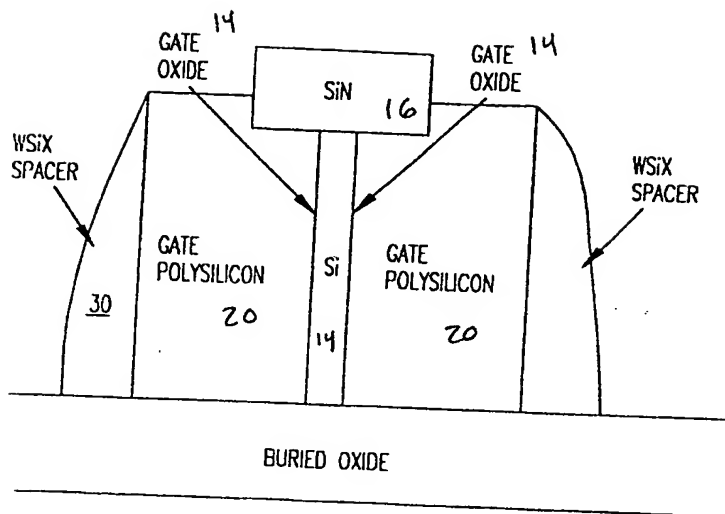


FIG. 3
(SECTION AA')

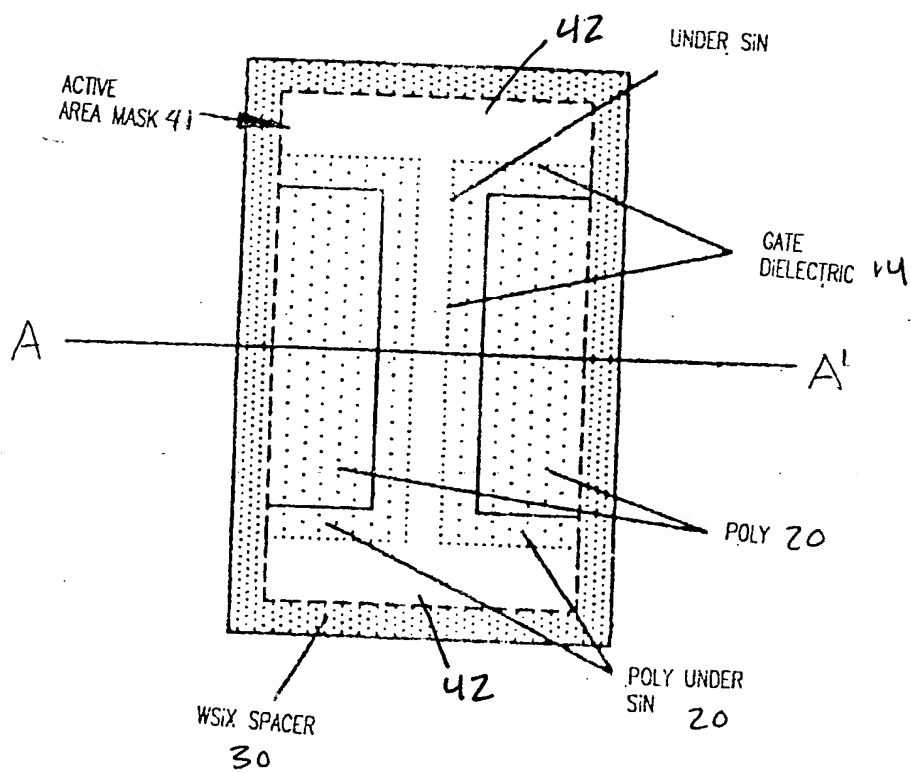


FIG. 3A

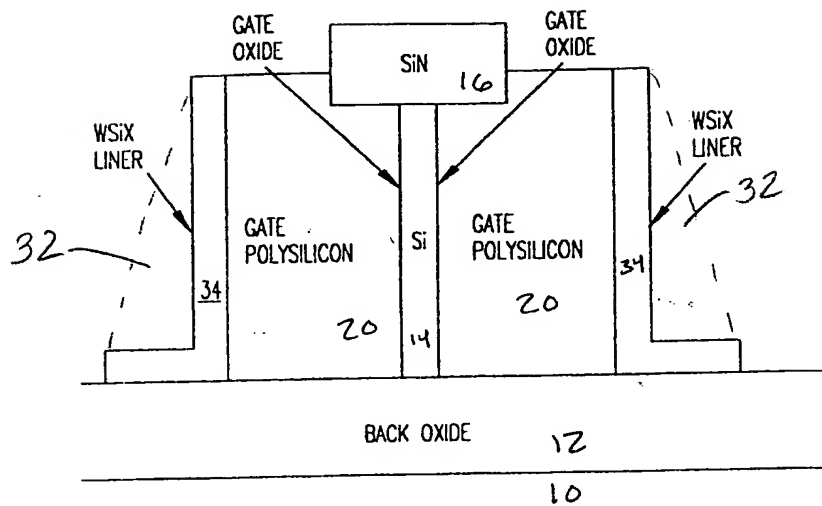


FIG. 3B
(SECTION AA')

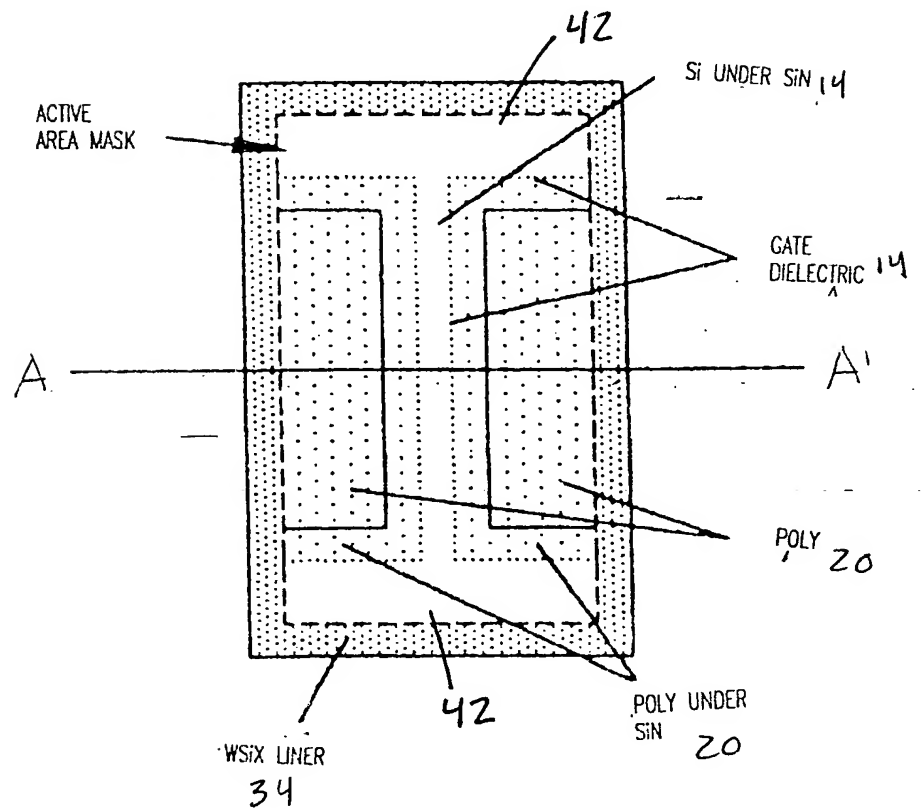


FIG. 3AB

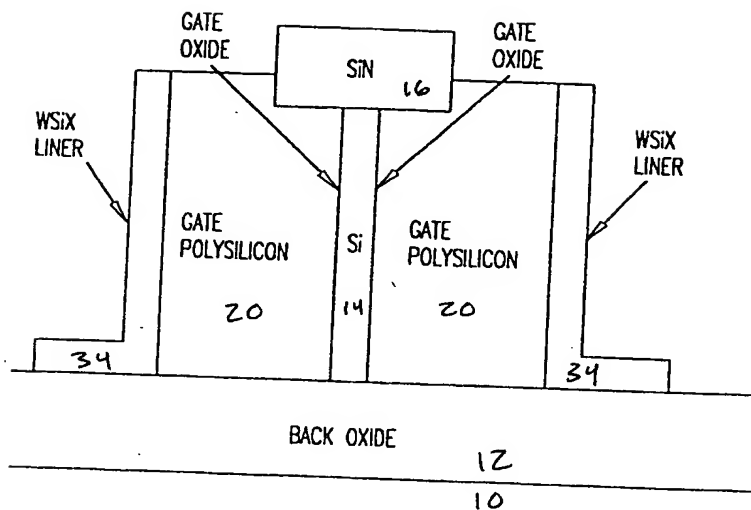


FIG. 4
(SECTION AA')

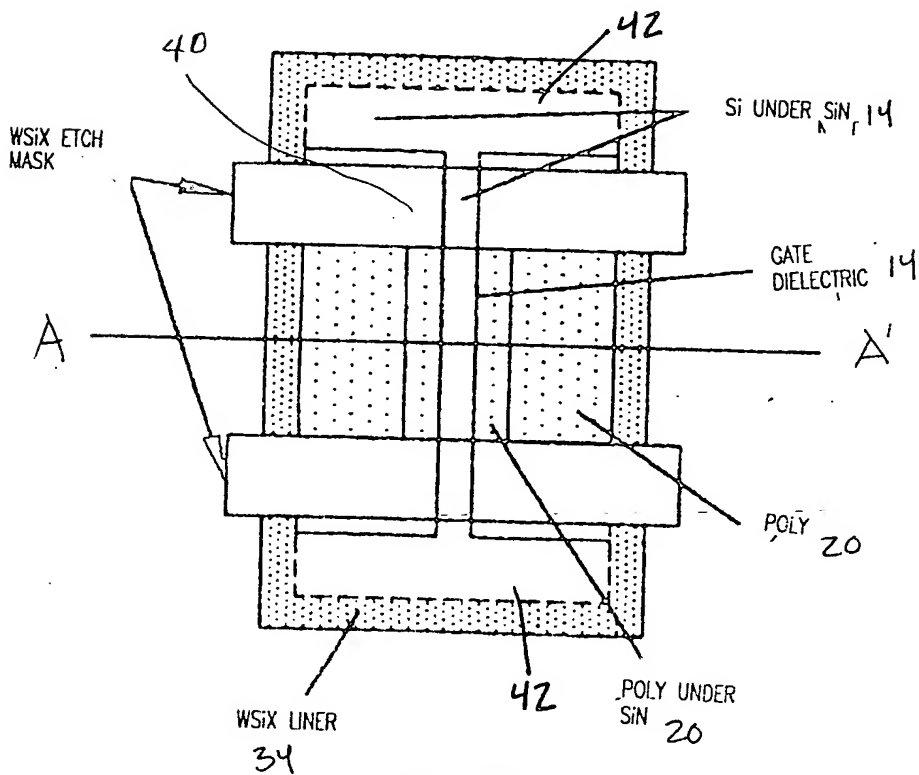


FIG. 4A

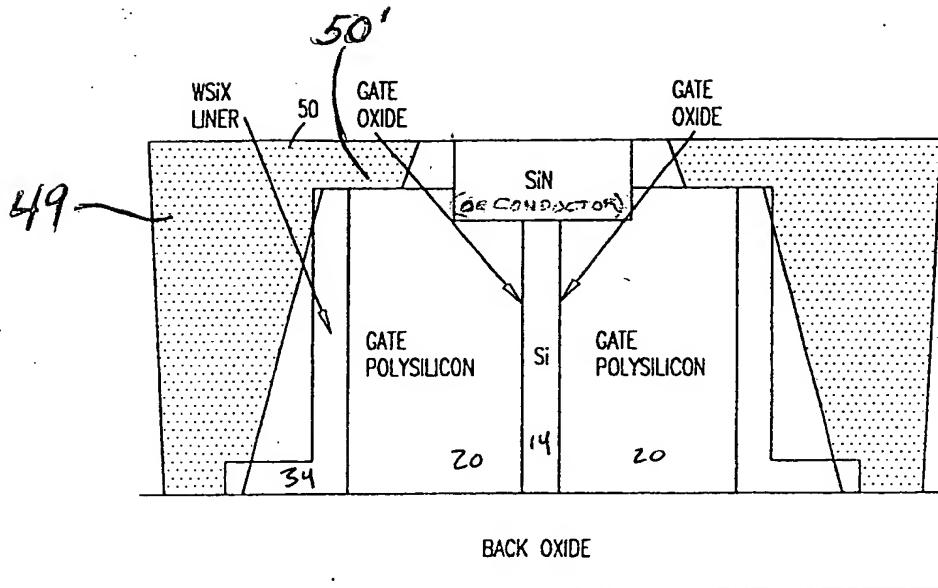


FIG. 5
(SECTION AA')

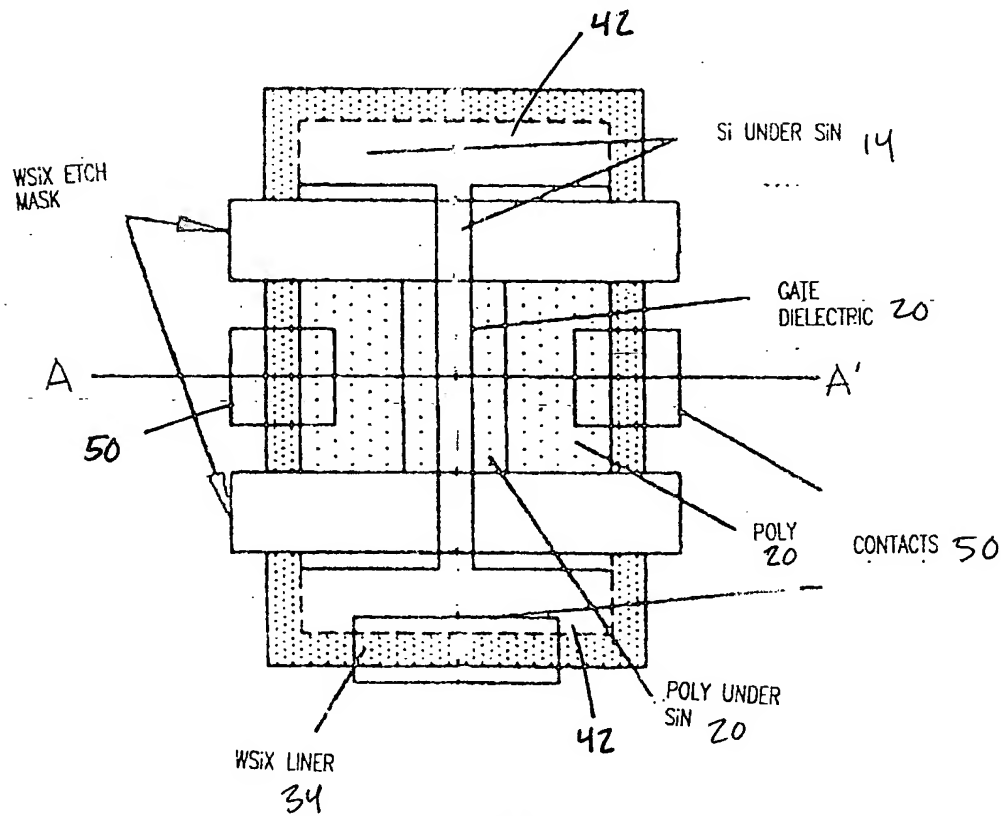


FIG. 5A

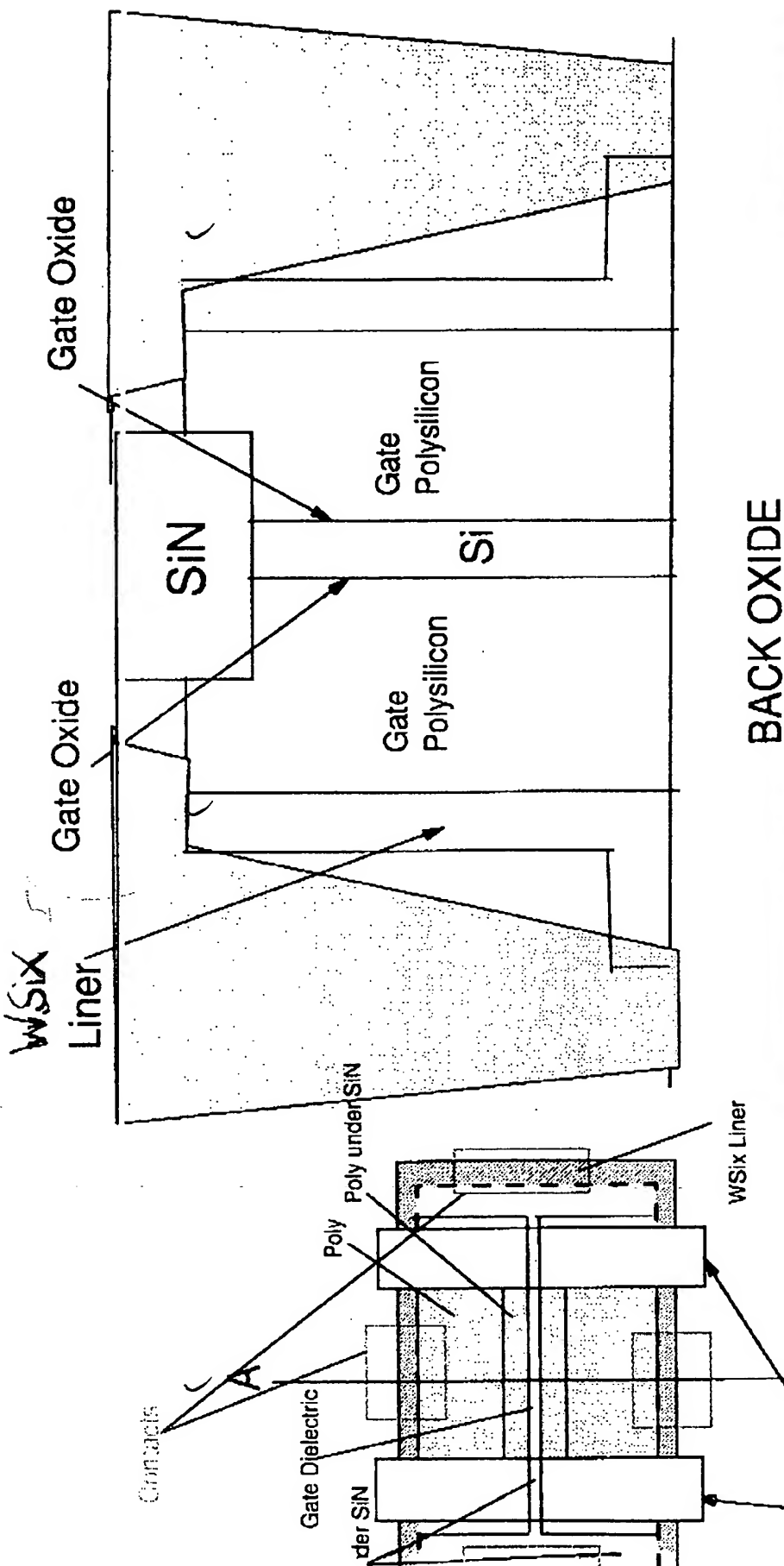


FIGURE 5 (Section AA')

* Standard STI processing is now performed. A damascene gate may be used to contact the gate polysilicon or contacts may be landed in the STI to contact the WSiX liner to make a connection to the gate. The source and drain is contacted with a standard contact process. Note that SiN is left only on top of the regions where the Si is present

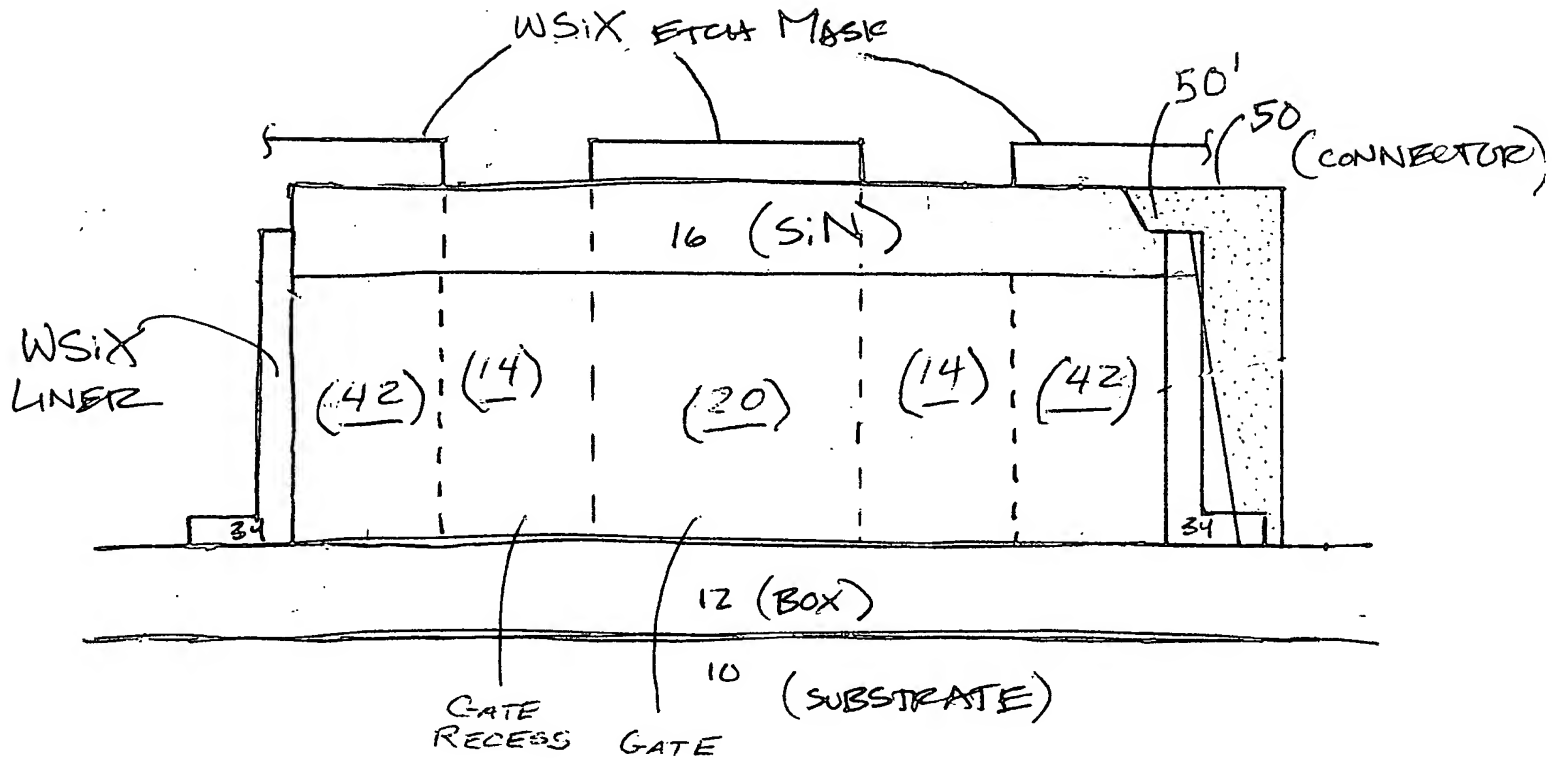


FIG. 5B